

74AHC3GU04

Inverter

Rev. 01 — 5 March 2004

Product data sheet

1. General description

The 74AHC3GU04 is a high-speed Si-gate CMOS device. This device provides the inverting single stage function.

2. Features

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-A exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101 exceeds 1000 V.
- Low power dissipation
- Balanced propagation delays
- SOT505-2 and SOT765-1 package
- Output capability ± 8 mA drive
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C.

3. Quick reference data

Table 1: Quick reference data
 $GND = 0$ V; $T_{amb} = 25$ °C; $t_r = t_f \leq 3.0$ ns.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHL} , t_{PLH}	propagation delay nA to nY	$V_{CC} = 5$ V; $C_L = 15$ pF	-	2.5	5.5	ns
C_I	input capacitance		-	3.0	10	pF
C_{PD}	power dissipation capacitance		^[1] - ^[2]	4	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] The condition is $V_i = GND$ to V_{CC} .

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4. Ordering information

Table 2: Ordering information

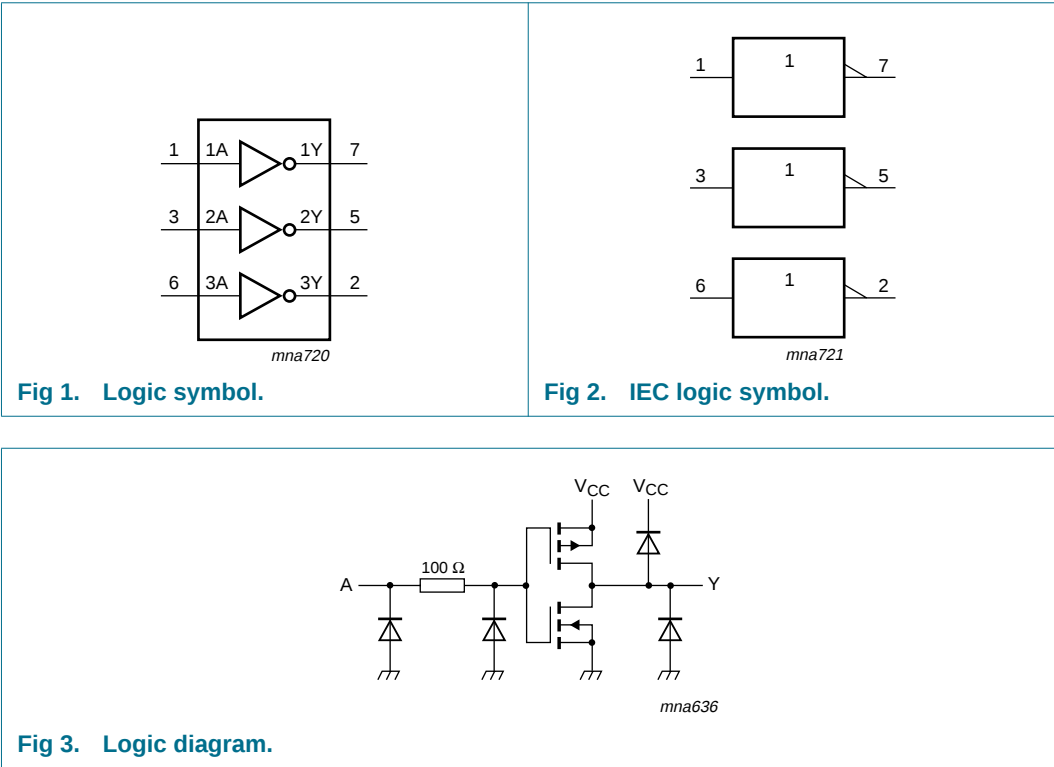
Type number	Package			
	Temperature range	Name	Description	Version
74AHC3GU04DP	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC3GU04DC	−40 °C to +125 °C	VSSOP8	plastic shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

5. Marking

Table 3: Marking

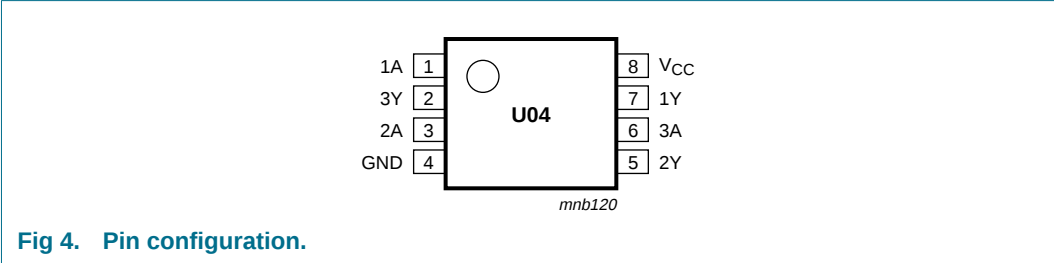
Type number	Marking code
74AHC3GU04DP	AU04
74AHC3GU04DC	AU4

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 4: Pin description

Pin	Symbol	Description
1	1A	data input
2	3Y	data output
3	2A	data input
4	GND	ground (0 V)
5	2Y	data output
6	3A	data input
7	1Y	data output
8	V _{CC}	supply voltage

8. Functional description

8.1 Function table

Table 5: Function table ^[1]

Input nA	Output nY
L	H
H	L

[1] H = HIGH voltage level;
L = LOW voltage level.

9. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	supply voltage		-0.5	+7.0	V
I_{IK}	input diode current	$V_I < -0.5$ V	-	-20	mA
I_{OK}	output diode current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	±20	mA
I_O	output source or sink current	$V_O > -0.5$ V or $V_O < V_{CC} + 0.5$ V	-	±25	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	±75	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40$ °C to +125 °C	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

10. Recommended operating conditions

Table 7: Recommended operating operations

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	operating ambient temperature	see Section 11 and Section 12	-40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 3.3$ V ± 0.3 V	-	-	100	ns/V
		$V_{CC} = 5$ V ± 0.5 V	-	-	20	ns/V

11. Static characteristics

Table 8: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.7	-	-	V
		V _{CC} = 3.0 V	2.4	-	-	V
		V _{CC} = 5.5 V	4.4	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.3	V
		V _{CC} = 3.0 V	-	-	0.6	V
		V _{CC} = 5.5 V	-	-	1.1	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		V _{CC} = 2.0 V; I _O = -50 µA	1.9	2.0	-	V
		V _{CC} = 3.0 V; I _O = -50 µA	2.9	3.0	-	V
		V _{CC} = 4.5 V; I _O = -50 µA	4.4	4.5	-	V
		V _{CC} = 3.0 V; I _O = -4.0 mA	2.58	-	-	V
		V _{CC} = 4.5 V; I _O = -8.0 mA	3.94	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		V _{CC} = 2.0 V; I _O = 50 µA	-	0	0.1	V
		V _{CC} = 3.0 V; I _O = 50 µA	-	0	0.1	V
		V _{CC} = 4.5 V; I _O = 50 µA	-	0	0.1	V
		V _{CC} = 3.0 V; I _O = 4.0 mA	-	-	0.36	V
		V _{CC} = 4.5 V; I _O = 8.0 mA	-	-	0.36	V
I _{LI}	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.1	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	µA
C _I	input capacitance		-	3.0	10	pF
T_{amb} = -40 °C to 85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.7	-	-	V
		V _{CC} = 3.0 V	2.4	-	-	V
		V _{CC} = 5.5 V	4.4	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.3	V
		V _{CC} = 3.0 V	-	-	0.6	V
		V _{CC} = 5.5 V	-	-	1.1	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -50 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -50 µA; V _{CC} = 3.0 V	2.9	-	-	V
		I _O = -50 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.48	-	-	V
		I _O = -8.0 mA; V _{CC} = 4.5 V	3.8	-	-	V

Table 8: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 50\ \mu\text{A}; V_{CC} = 2.0\ \text{V}$	-	-	0.1	V
		$I_O = 50\ \mu\text{A}; V_{CC} = 3.0\ \text{V}$	-	-	0.1	V
		$I_O = 50\ \mu\text{A}; V_{CC} = 4.5\ \text{V}$	-	-	0.1	V
		$I_O = 4.0\ \text{mA}; V_{CC} = 3.0\ \text{V}$	-	-	0.44	V
		$I_O = 8.0\ \text{mA}; V_{CC} = 4.5\ \text{V}$	-	-	0.44	V
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\ \text{V}$	-	-	1.0	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0\ \text{A}; V_{CC} = 5.5\ \text{V}$	-	-	10	μA
C_I	input capacitance		-	-	10	pF
$T_{amb} = -40\ ^\circ\text{C}$ to $+125\ ^\circ\text{C}$						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0\ \text{V}$	1.7	-	-	V
		$V_{CC} = 3.0\ \text{V}$	2.4	-	-	V
		$V_{CC} = 5.5\ \text{V}$	4.4	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0\ \text{V}$	-	-	0.3	V
		$V_{CC} = 3.0\ \text{V}$	-	-	0.6	V
		$V_{CC} = 5.5\ \text{V}$	-	-	1.1	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -50\ \mu\text{A}; V_{CC} = 2.0\ \text{V}$	1.9	-	-	V
		$I_O = -50\ \mu\text{A}; V_{CC} = 3.0\ \text{V}$	2.9	-	-	V
		$I_O = -50\ \mu\text{A}; V_{CC} = 4.5\ \text{V}$	4.4	-	-	V
		$I_O = -4.0\ \text{mA}; V_{CC} = 3.0\ \text{V}$	2.40	-	-	V
		$I_O = -8.0\ \text{mA}; V_{CC} = 4.5\ \text{V}$	3.70	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 50\ \mu\text{A}; V_{CC} = 2.0\ \text{V}$	-	-	0.1	V
		$I_O = 50\ \mu\text{A}; V_{CC} = 3.0\ \text{V}$	-	-	0.1	V
		$I_O = 50\ \mu\text{A}; V_{CC} = 4.5\ \text{V}$	-	-	0.1	V
		$I_O = 4.0\ \text{mA}; V_{CC} = 3.0\ \text{V}$	-	-	0.55	V
		$I_O = 8.0\ \text{mA}; V_{CC} = 4.5\ \text{V}$	-	-	0.55	V
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\ \text{V}$	-	-	2.0	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0\ \text{A}; V_{CC} = 5.5\ \text{V}$	-	-	40	μA
C_I	input capacitance		-	-	10	pF

12. Dynamic characteristics

Table 9: Dynamic characteristics

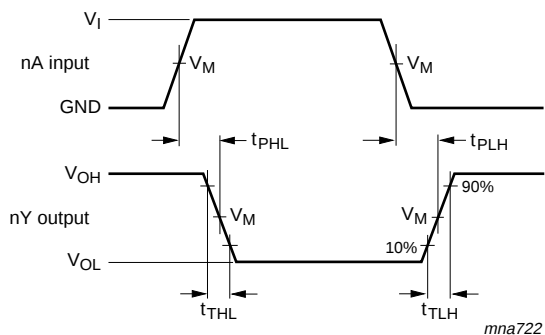
At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $t_r = t_f \leq 3.0$ ns. See [Figure 6](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t _{PHL} , t _{PLH}	propagation delay nA to nY	see Figure 5				
		V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF	[1] -	3.0	7.1	ns
		V _{CC} = 3.0 V to 3.6 V; C _L = 50 pF	[1] -	4.3	10.6	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 15 pF	[2] -	2.5	5.5	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 50 pF	[2] -	3.5	7.0	ns
T_{amb} = -40 °C to 85 °C						
t _{PHL} , t _{PLH}	propagation delay nA to nY	see Figure 5				
		V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF	1.0	-	8.5	ns
		V _{CC} = 3.0 V to 3.6 V; C _L = 50 pF	1.0	-	12.0	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 15 pF	1.0	-	6.0	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 50 pF	1.0	-	8.0	ns
T_{amb} = -40 °C to 125 °C						
t _{PHL} , t _{PLH}	propagation delay nA to nY	see Figure 5				
		V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF	1.0	-	10.0	ns
		V _{CC} = 3.0 V to 3.6 V; C _L = 50 pF	1.0	-	13.5	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 15 pF	1.0	-	7.0	ns
		V _{CC} = 4.5 V to 5.5 V; C _L = 50 pF	1.0	-	9.0	ns

[1] Typical values are measured at V_{CC} = 3.3 V.

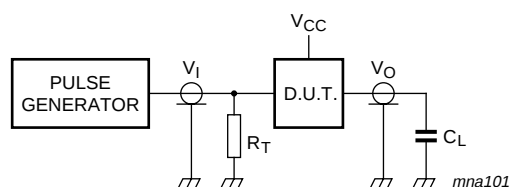
[2] Typical values are measured at V_{CC} = 5.0 V.

13. AC waveforms



$V_M = 50\%$; $V_I = \text{GND to } V_{CC}$.

Fig 5. Input (nA) to output (nY) propagation delays.



Definitions for test circuit:

C_L = load capacitance including jig and probe capacitance. (See [Section 12](#) for values).

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times.

13.1 Typical transfer characteristics

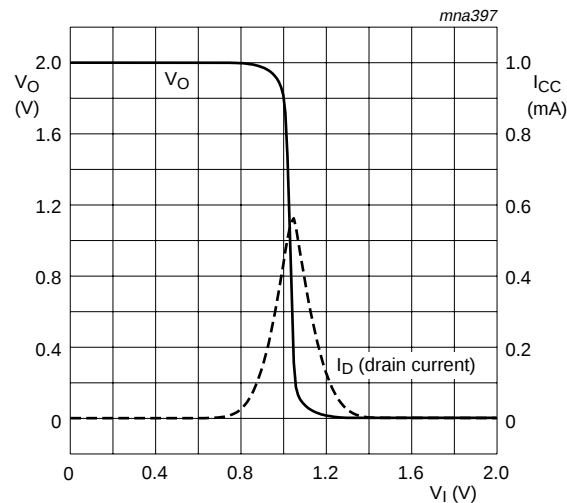


Fig 7. $V_{CC} = 2.0\text{ V}$; $I_O = 0\text{ A}$.

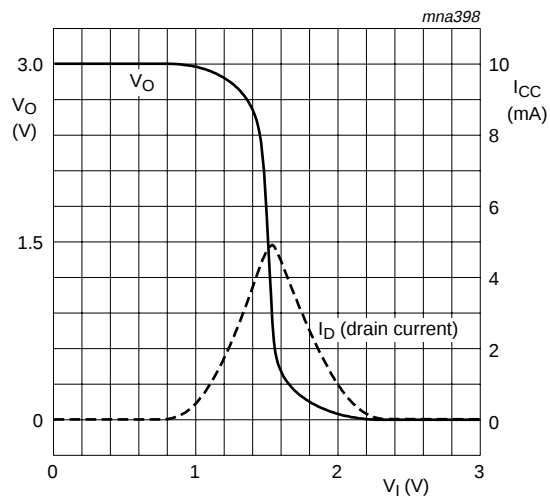


Fig 8. $V_{CC} = 3.0\text{ V}$; $I_O = 0\text{ A}$.

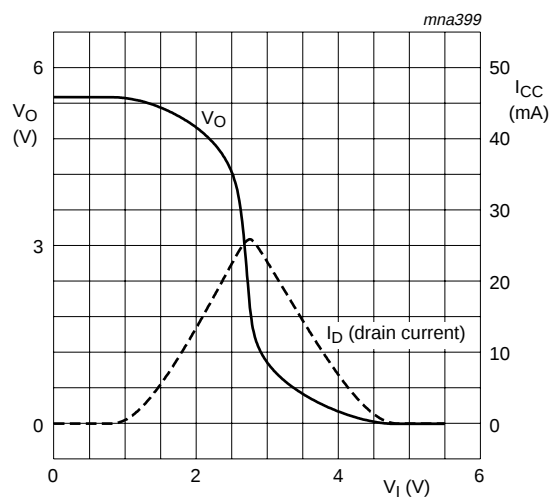
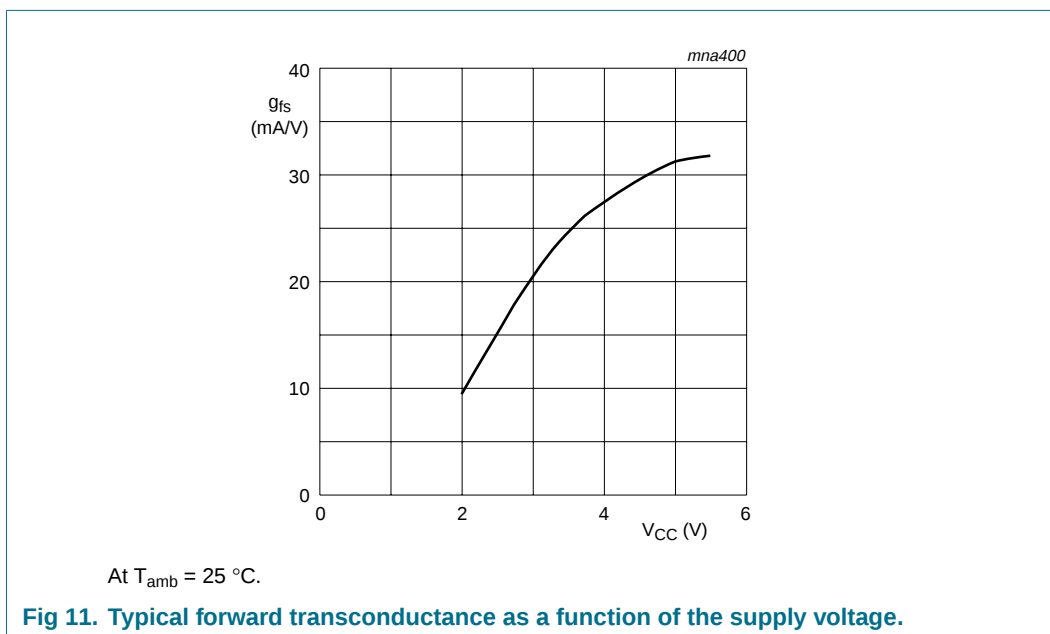
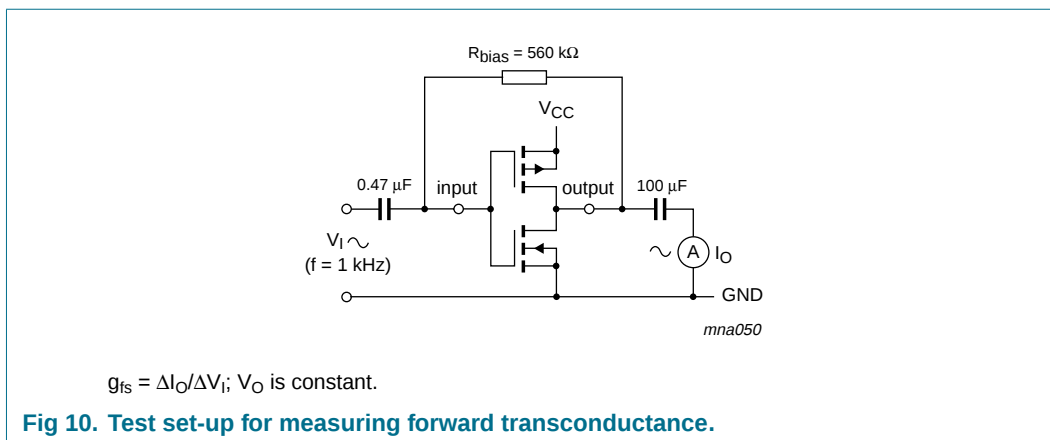


Fig 9. $V_{CC} = 5.5\text{ V}$; $I_O = 0\text{ A}$.

13.2 Forward transconductance



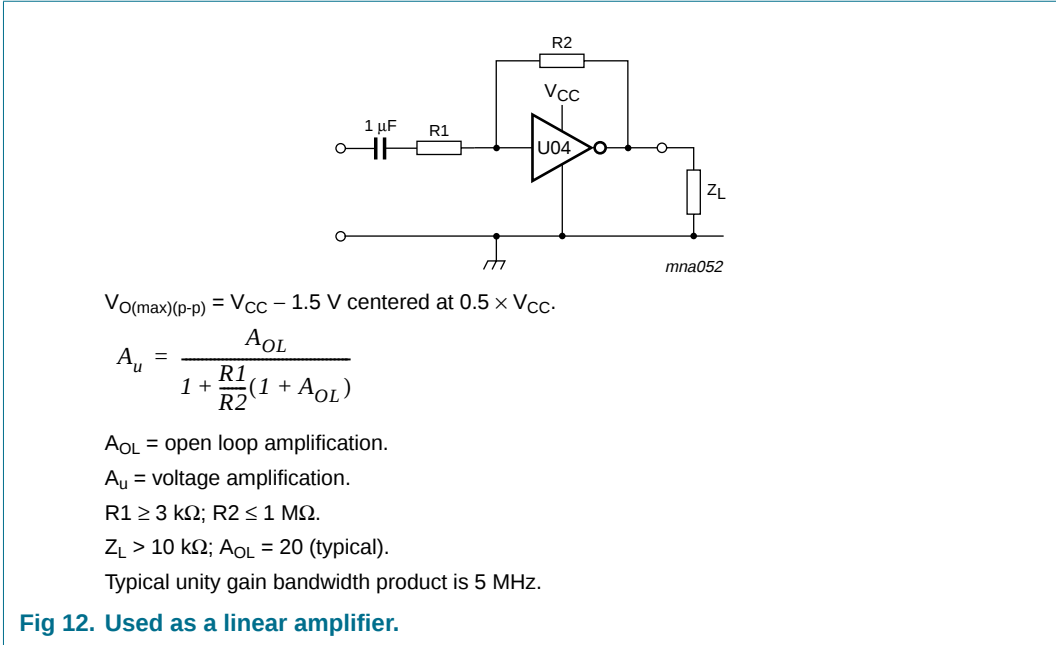
14. Application information

Some applications are:

- Linear amplifier see [Figure 12](#)
- In crystal oscillator design see [Figure 13](#).

Remark: All values given are typical unless otherwise specified.

14.1 Linear amplifier



14.2 Crystal oscillator

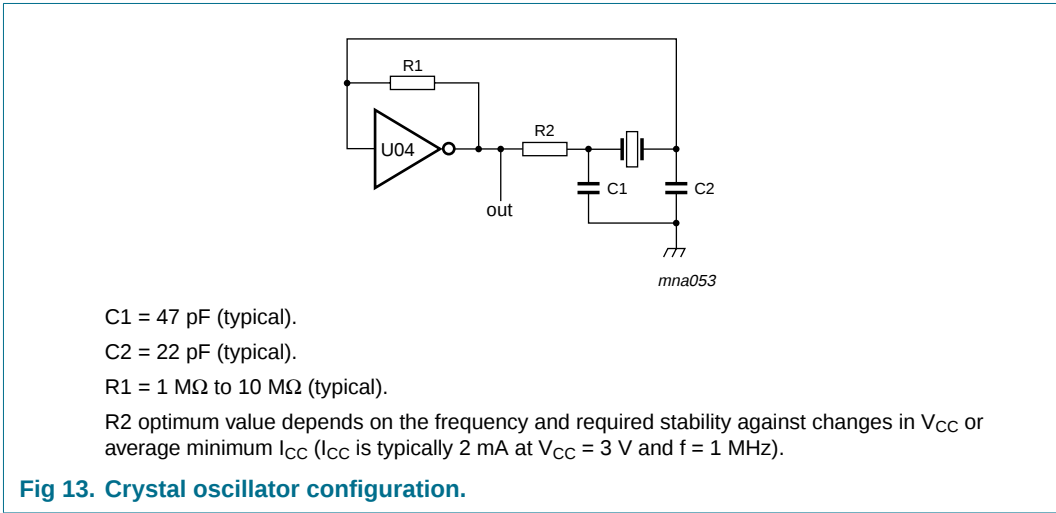


Table 10: External components for resonator (f < 1 MHz)

Frequency (kHz)	R1 (MΩ)	R2 (kΩ)	C1 (pF)	C2 (pF)
10 to 15.9	22	220	56	20
16 to 24.9	22	220	56	10
25 to 54.9	22	100	56	10
55 to 129.9	22	100	47	5
130 to 199.9	22	47	47	5
200 to 349.9	22	47	47	5
350 to 600	22	47	47	5

Remark: All values given are typical and must be used as initial set-up.

Table 11: Optimum value for R2

Frequency (kHz)	R2 (k Ω)	Optimum for
3	2.0	minimum required I _{CC}
	8.0	minimum influence due to change in V _{CC}
6	1.0	minimum required I _{CC}
	4.7	minimum influence due to change in V _{CC}
10	0.5	minimum required I _{CC}
	2.0	minimum influence due to change in V _{CC}
14	0.5	minimum required I _{CC}
	1.0	minimum influence due to change in V _{CC}
>14	-	replace R2 by C3 with a typical value of 35 pF

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

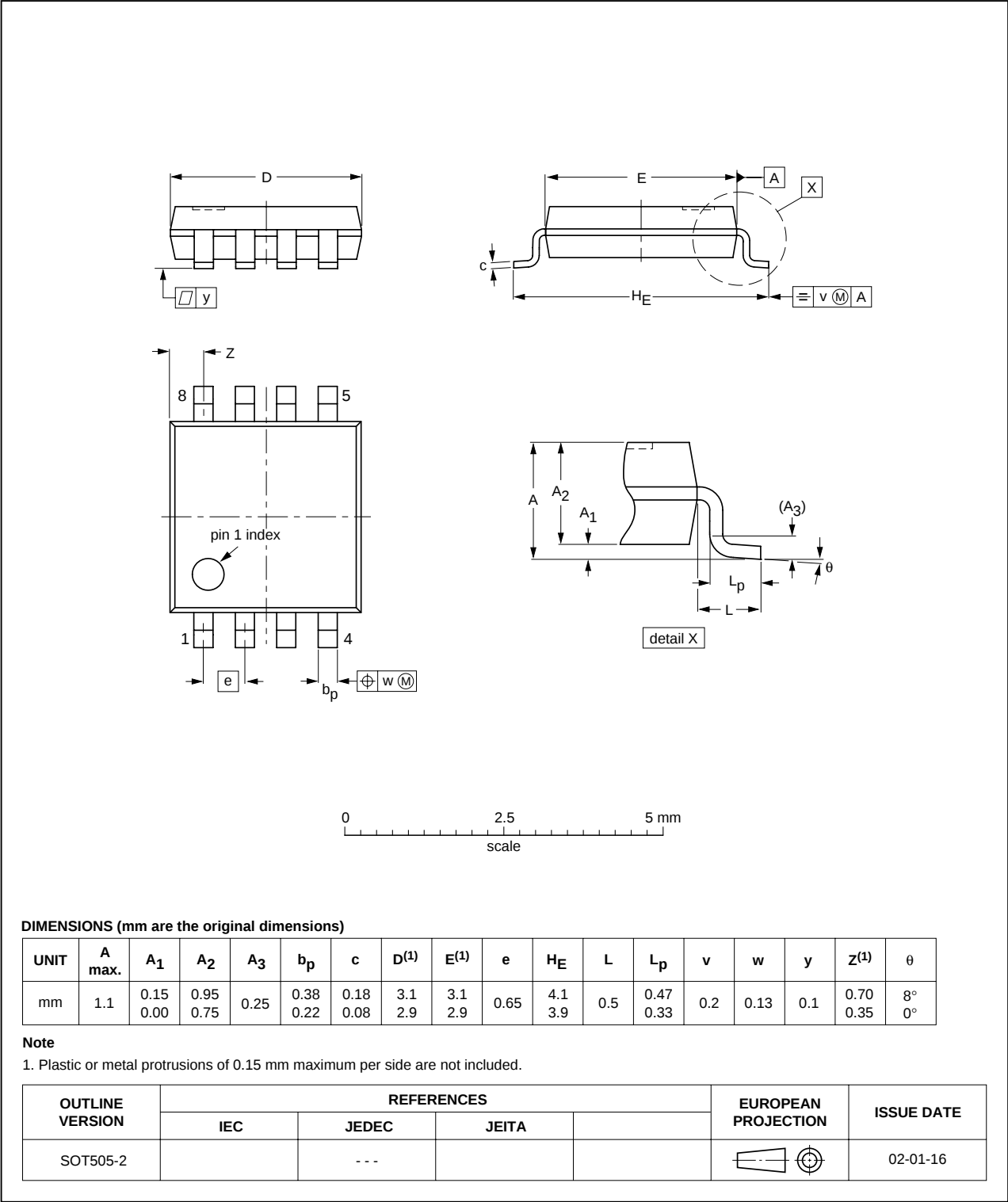


Fig 14. Package outline TSSOP8.

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

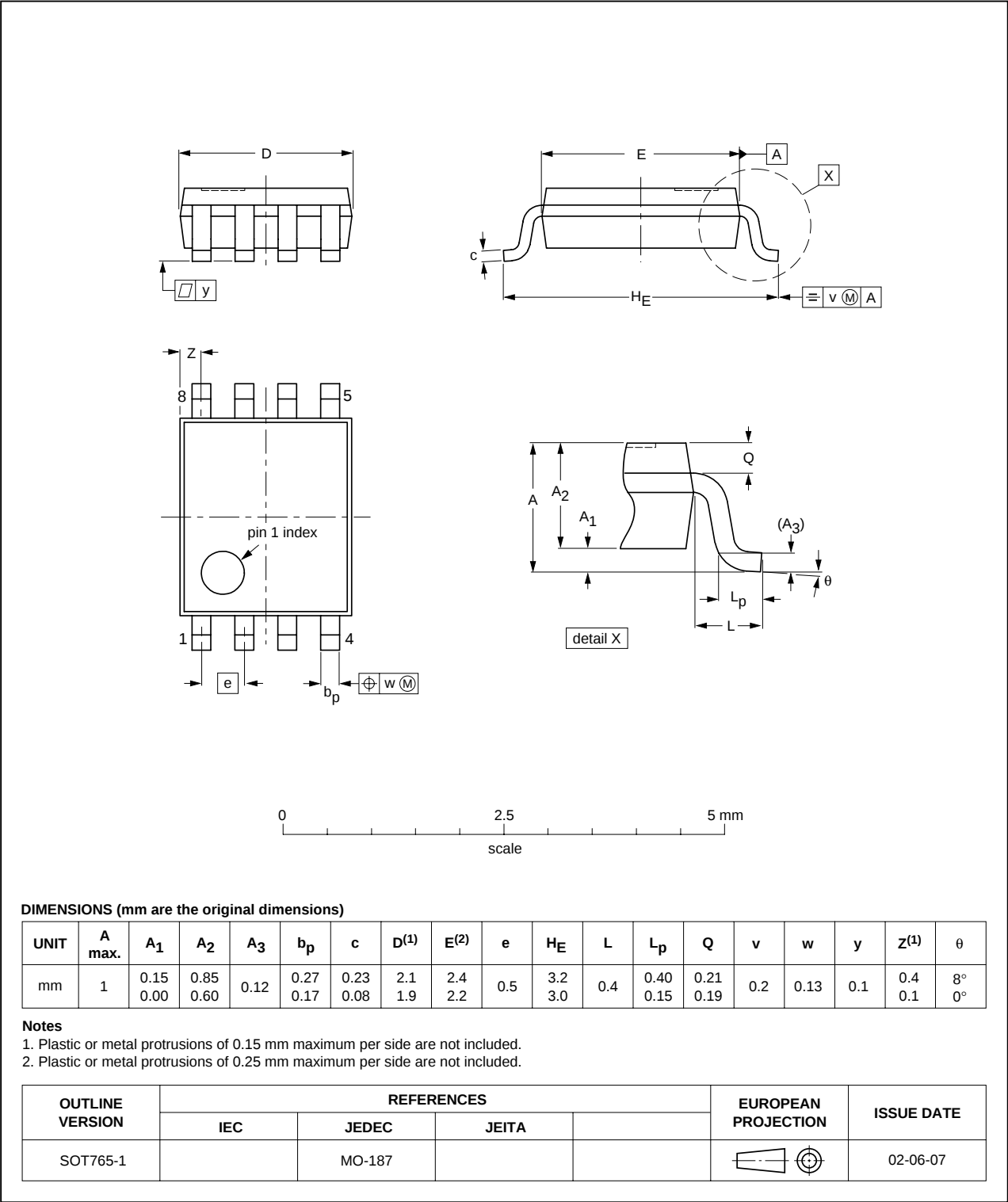


Fig 15. Package outline VSSOP8.

16. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
74AHC3GU04_1	20040305	product data	-	9397 750 12754	-

17. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

18. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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